

SAMSUNG SEMICONDUCTOR INC

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MMBC1623L6 NPN EPITAXIAL SILICON TRANSISTOR

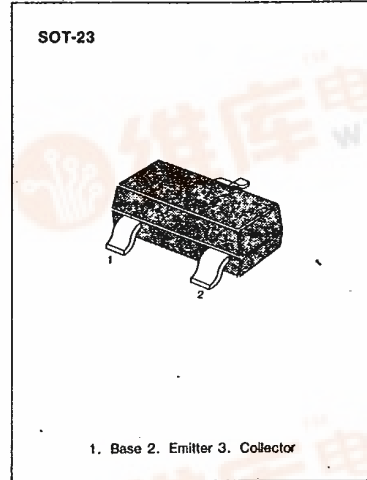
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AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base Voltage	V _{EB0}	5.0	V
Collector Current	I _c	100	mA
Collector Dissipation	P _c	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBC1623L3 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} =40V, I _E =0		100	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0		100	nA
DC Current Gain	h _{FE}	V _{CE} =6V, I _C =1.0mA	200	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA		0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA		1.0	V
Base-Emitter On Voltage	V _{BE(on)}	I _C =1.0mA, V _{CE} =6V	0.6	0.7	V
Current Gain-Bandwidth Product	f _T	V _{CE} =6V, I _E =10mA f=100MHz	200		MHz

Marking

